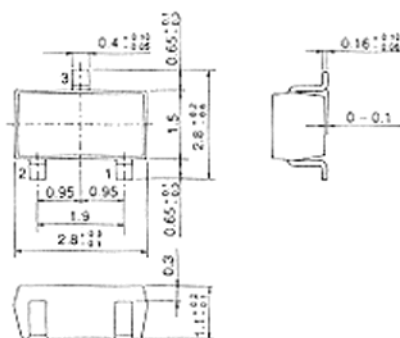


2SC2620

SILICON NPN EPITAXIAL PLANAR
VHF AMPLIFIER, LOCAL OSCILLATOR



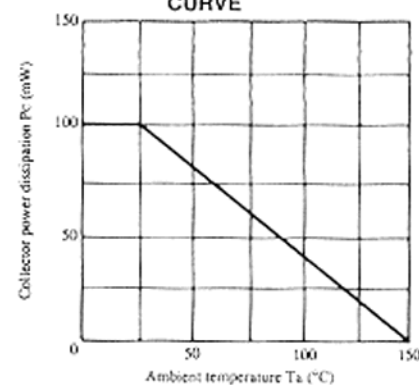
(MPAK)

1. Emitter
2. Base
3. Collector
(Dimensions in mm)

■ ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

Item	Symbol	2SC2620	Unit
Collector to base voltage	V_{CB0}	30	V
Collector to emitter voltage	V_{CE0}	20	V
Emitter to base voltage	V_{EB0}	4	V
Collector current	I_C	20	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

MAXIMUM COLLECTOR DISSIPATION CURVE

■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	$V_{(BR)CB0}$	$I_C = 10\mu\text{A}$, $I_E = 0$	30	—	—	V
Collector to emitter breakdown voltage	$V_{(BR)CE0}$	$I_C = 1\text{mA}$, $R_{BE} = \infty$	20	—	—	V
Emitter to base breakdown voltage	$V_{(BR)EB0}$	$I_E = 10\mu\text{A}$, $I_C = 0$	4	—	—	V
Collector cutoff current	I_{CB0}	$V_{CB} = 10\text{V}$, $I_E = 0$	—	—	0.5	μA
Emitter cutoff current	I_{EB0}	$V_{EB} = 2\text{V}$, $I_C = 0$	—	—	0.5	μA
DC current transfer ratio	h_{FE}^*	$V_{CE} = 6\text{V}$, $I_C = 1\text{mA}$	60	—	200	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 20\text{mA}$, $I_B = 4\text{mA}$	—	0.17	—	V
Base to emitter voltage	V_{BE}	$V_{CE} = 6\text{V}$, $I_C = 1\text{mA}$	—	0.72	—	V
Gain bandwidth product	f_T	$V_{CE} = 6\text{V}$, $I_C = 5\text{mA}$	—	940	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$	—	0.9	—	pF

* The 2SC2620 is grouped by h_{FE} as follows.

Grade	B	C
Mark	QB	QC
hFE	60 to 120	100 to 200

■ See characteristic curves of 2SC535.